C2

9. (Amended) A method of manufacturing a semiconductor device having a plurality of thin film transistors, comprising the steps of:

forming a semiconductor film comprising silicon on an insulating surface;

crystallizing said semiconductor film; and

oxidizing the crystallized semiconductor film to be active layers of said thin film transistors in a pressurized atomsphere at a temperature of 500 to 650°C.

C3

17. (Amended) A method of manufacturing a semiconductor device having a plurality of thin film transistors, comprising the steps of:

forming a semiconductor film comprising silicon over an alkali-free glass substrate;

crystallizing said semiconductor film; and

oxidizing the crystallized semiconductor film to be active layers of said thin film transistors in a pressurized atmosphere at a temperature lower than a strain point of said glass substrate.

C4

25. (Amended) A method of manufacturing a semiconductor device having a plurality of thin film transistors, comprising the steps of:

forming a semiconductor film comprising silicon over a glass substrate;

crystallizing said semiconductor film;

forming an insulating film adjacent to said crystallized semiconductor film by plasma CVD; and

forming gate electrodes adjacent to said insulating film,

wherein said method further comprises a step of oxidizing the crystallized semiconductor film to be active layers of said thin film transistors in a pressurized

C4

atmosphere at a temperature lower than a strain point of said glass substrate.

33. (Amended) A method of manufacturing a semiconductor device having a plurality of thin film transistors, comprising the steps of:

C5

forming a semiconductor film comprising silicon on an insulating surface;

crystallizing said semiconductor film;

forming an insulating film adjacent to said crystallized semiconductor film by plasma CVD; and

forming gate electrodes adjacent to said insulating film,

wherein said method further comprises a step of oxidizing the crystallized semiconductor film to be active layers of said thin film transistors in a pressurized atomsphere at a temperature of 500 to 650°C.

41. (Amended) A method of manufacturing a semiconductor device having a plurality of thin film transistors, comprising the steps of:

C6

forming a semiconductor film comprising silicon over an alkali-free glass substrate;

crystallizing said semiconductor film;

forming an insulating film adjacent to said crystallized semiconductor film by plasma CVD; and

forming gate electrodes adjacent to said insulating film,

wherein said method further comprises a step of oxidizing the crystallized semiconductor film to be active layers of said thin film transistors in a pressurized atmosphere at a temperature lower than a strain point of said glass substrate.

C7

49. (Amended) A method of manufacturing a semiconductor device having a plurality of thin film transistors, comprising the steps of:

forming a semiconductor film comprising silicon over a glass substrate;

crystallizing said semiconductor film; and

oxidizing the crystallized semiconductor film to be active layers of said thin film transistors in a pressurized atmosphere of a pressure of 1 to 15 atms,

wherein said oxidizing the semiconductor film is performed in a temperature lower than a strain point of said glass substrate.

C8

56. (Amended) A method of manufacturing a semiconductor device having a plurality of thin film transistors, comprising the steps of:

forming a semiconductor film comprising silicon on an insulating surface;

crystallizing said semiconductor film; and

oxidizing the crystallized semiconductor film to be active layers of said thin film transistors in a pressurized atmosphere of a pressure of 1 to 15 atms,

wherein said oxidizing the semiconductor film is performed in a temperature of 500 to 650°C.

C9

63. (Amended) A method of manufacturing a semiconductor device having a plurality of thin film transistors, comprising the steps of:

forming a semiconductor film comprising silicon over an alkali-free glass substrate;

crystallizing said semiconductor film; and

oxidizing the crystallized semiconductor film to be active layers of said thin film transistors in pressurized atmosphere of a pressure of 1 to 15 atms, for elactrically

C9

isolating said plurality of thin film transistors from one another,

wherein said oxidizing the semiconductor film is performed in a temperature lower than a strain point of said glass substrate.

C10

70. (Amended) A method of manufacturing a semiconductor device having a plurality of thin film transistors, comprising the steps of:

forming a semiconductor film comprising silicon over a glass substrate;

crystallizing said semiconductor film;

forming an insulating film adjacent to said crystallized semiconductor film; and

forming gate electrodes adjacent to said insulating film,

wherein said method further comprises a step of oxidizing the crystallized semiconductor film to be active layers of said thin film transistors in a pressurized atmosphere of a pressure of 1 to 15 atms, and

wherein said oxidizing the semiconductor film is performed in a temperature lower than a strain point of said glass substrate.

C11

78. (Amended) A method of manufacturing a semiconductor device having a plurality of thin film transistors, comprising the steps of:

forming a semiconductor film comprising silicon on an insulating surface;

crystallizing said semiconductor film;

forming an insulating film adjacent to said crystallized semiconductor film; and

forming gate electrodes adjacent to said insulating film,

wherein said method further comprises a step of oxidizing the crystallized semiconductor film to be active layers of said thin film transistors in a pressurized atmosphere of at a pressure of 1 to 15 atms, and